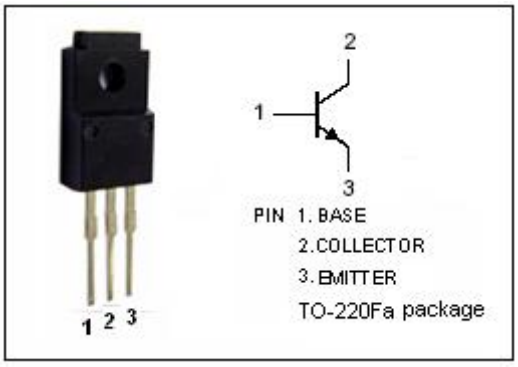
isc Silicon NPN Power Transistor — 2SC3297



DESCRIPTION

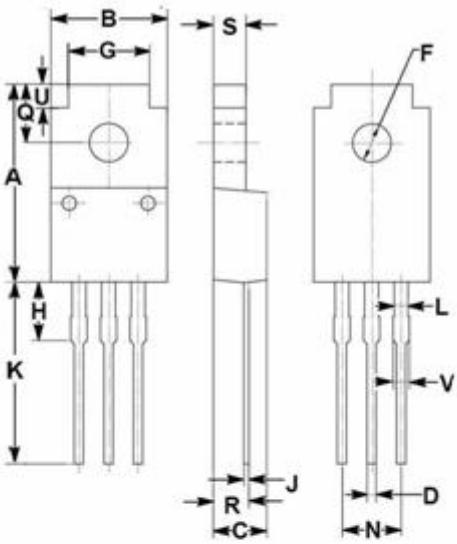
- Collector-Emitter Breakdown Voltage
  : $V_{(BR)CEO}$= 30V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SA1305
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power amplifier applications.
- Car radio, car stereo output stage amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	3	A
I_B	Base Current-Continuous	0.3	A
P_C	Total Power Dissipation @ T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	30			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.2A			0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 0.5A; V_{CE}= 2V			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 20V; I_E= 0			1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			1.0	μA
h_{FE-1}	DC Current Gain	I_C= 0.5A; V_{CE}= 2V	70		240	
h_{FE-2}	DC Current Gain	I_C= 2.5A; V_{CE}= 2V	25			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 2V		100		MHz
C_{OB}	Output Capacitance	I_E=0; V_{CB}= 10V; f_{test}= 1.0MHz		35		pF

◆ **h_{FE-1} Classifications**

O	Y
70-140	120-240